TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSII⁻⁵)

2SK1930

Chopper Regulator, DC–DC Converter, and Motor Drive Applications

- Low drain-source ON resistance $: RDS (ON) = 3.0 \Omega (typ.)$
- High forward transfer admittance : $|Y_{fs}| = 2.0 \text{ S} (typ.)$
- Low leakage current $: I_{DSS} = 300 \ \mu A \ (max) \ (V_{DS} = 800 \ V)$
- Enhancement mode $: V_{th} = 1.5 \sim 3.5 \text{ V} (V_{DS} = 10 \text{ V}, \text{ ID} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	1000	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	1000	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	۱ _D	4	А	
	Pulse (Note 1)	I _{DP}	12	~	
Drain power dissipation (Tc = 25°C)		PD	100	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

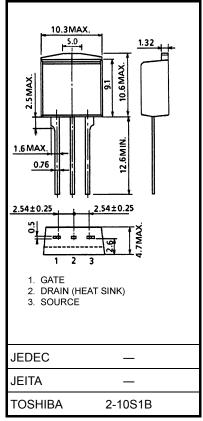
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

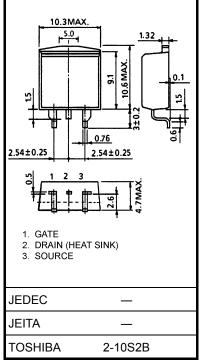
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch–c)}	1.25	°C / W
Thermal resistance, channel to ambient	R _{th (ch–a)}	83.3	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



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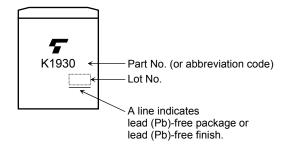
Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V	_		±100	nA
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 800 V, V _{GS} = 0 V		_	300	μA
Drain−source br voltage	eakdown	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	1000	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	V
Drain-source Ol	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 2 A	-	3.0	3.8	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 20 V, I _D = 2 A	1.0	2.0	_	S
Input capacitance	e	C _{iss}			700	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	55	_	pF
Output capacitance		C _{oss}			100		
Switching time	Rise time	tr	$V_{GS} \stackrel{10V}{}_{0V} \int_{C_{c}} I_{D} = 2A$ $V_{GS} \stackrel{VOUT}{}_{0V} \int_{C_{c}} I_{D} = 2A$ $R_{L} = 200\Omega$	_	18	_	
	Turn-on time	t _{on}		-	30		
	Fall time	t _f		_	12	_	ns
	Turn-off time	t _{off}	$V_{DD} = 400V$ Duty $\leq 1\%$, t _w = 10 μ s	_	70	_	
Total gate charge (Gate-source plus gate-drain)		Qg			60	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 4 A		35	_	nC
Gate-drain ("miller") charge		Q _{gd}			25	_	

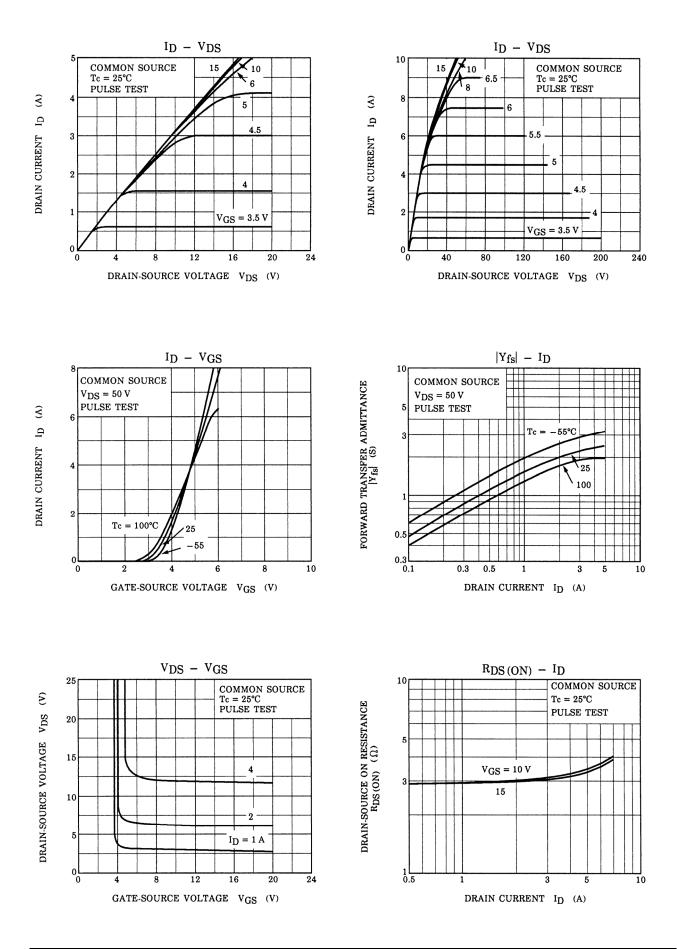
Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	-	_	4	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	Ι		12	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 4 A, V _{GS} = 0 V	_		-1.9	V

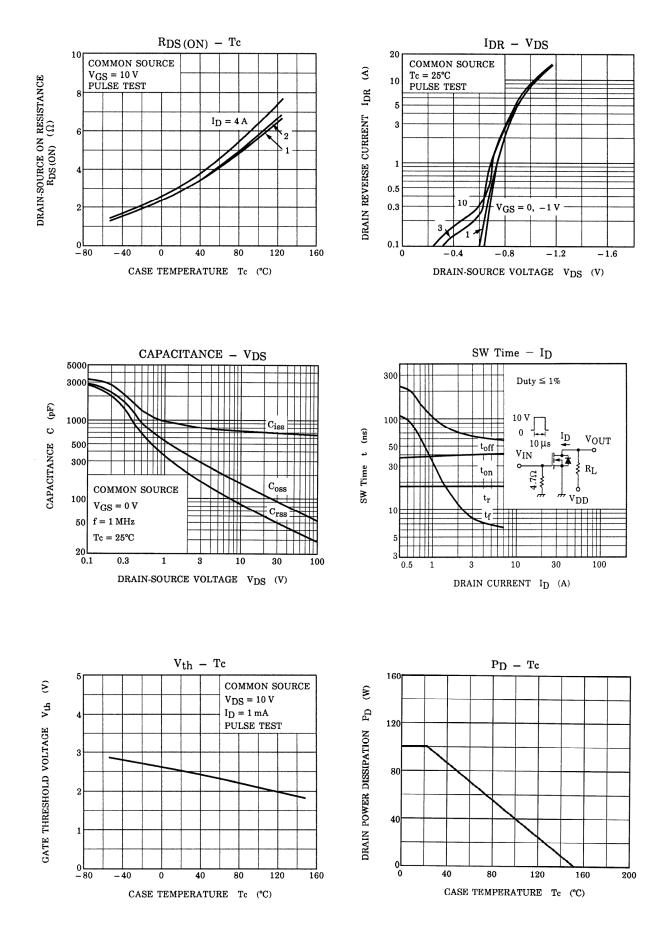
Marking

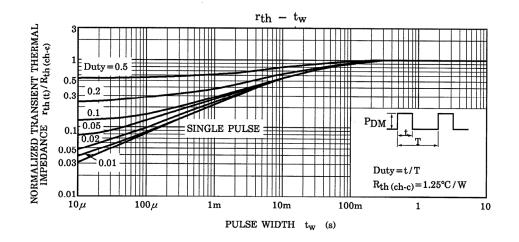


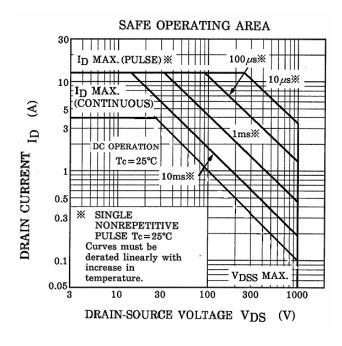
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